



# STS6DNF30V

## DUAL N-CHANNEL 30V - 0.026Ω - 6A SO-8 2.5V-DRIVE STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STS6DNF30V	30 V	<0.030Ω (@4.5V) <0.038Ω (@2.5V)	6 A

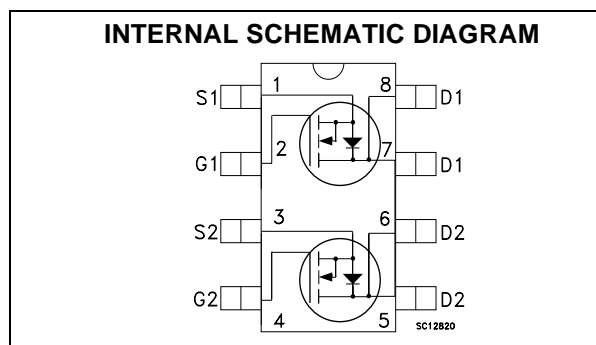
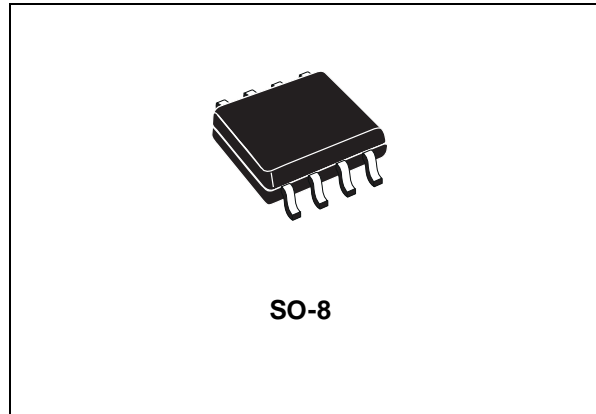
- TYPICAL R<sub>DS(on)</sub> = 0.026Ω (@4.5V)
- TYPICAL R<sub>DS(on)</sub> = 0.030Ω (@2.5V)
- ULTRA LOW THRESHOLD GATE DRIVE (2.5V)
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY

### DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

- BATTERY SAFETY UNIT IN NOMADIC EQUIPMENT
- DC-DC CONVERTERS
- POWER MANAGEMENT IN PORTABLE/ DESKTOP PCs



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	30	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	30	V
V <sub>GS</sub>	Gate- source Voltage	±12	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C Single Operation	6	A
	Drain Current (continuous) at T <sub>C</sub> = 100°C Single Operation	3.8	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	24	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C Dual Operation	2	W
	Total Dissipation at T <sub>C</sub> = 25°C Single Operation	1.6	W

(●) Pulse width limited by safe operating area

## STS6DNF30V

### THERMAL DATA

Rthj-amb	Thermal Resistance Junction-ambient Max Single Operation Thermal Resistance Junction-ambient Max Dual Operation	78 62.5	°C/W °C/W
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±12V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.6			V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3 A V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 3 A		0.026 0.030	0.030 0.038	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 3 A		15		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, f = 1 MHz, V <sub>GS</sub> = 0		800		pF
C <sub>oss</sub>	Output Capacitance			180		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			32		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}, I_D = 3\text{ A}$		20		ns
$t_r$	Rise Time	$R_G = 4.7\Omega, V_{GS} = 2.5\text{ V}$ (see test circuit, Figure 3)		25		ns
$Q_g$	Total Gate Charge	$V_{DD} = 15\text{ V}, I_D = 6\text{ A},$		6.8	9.5	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 2.5\text{ V}$		2		nC
$Q_{gd}$	Gate-Drain Charge			3.4		nC

**SWITCHING OFF**

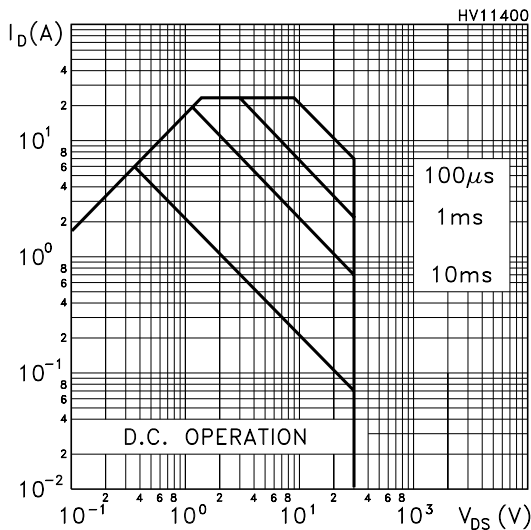
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 10\text{ V}, I_D = 3\text{ A},$		32		ns
$t_f$	Fall Time	$R_G = 4.7\Omega, V_{GS} = 2.5\text{ V}$ (see test circuit, Figure 3)		13		ns

**SOURCE DRAIN DIODE**

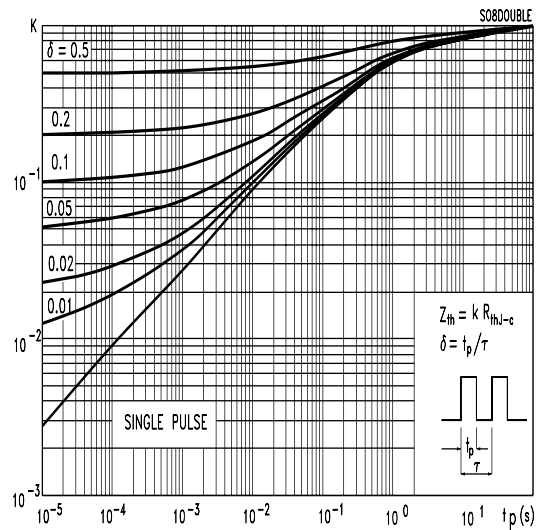
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				6	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				24	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 6\text{ A}, V_{GS} = 0$			1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 6\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$		25		ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD} = 15\text{ V}, T_j = 150^\circ\text{C}$		21		nC
$I_{RRM}$	Reverse Recovery Current	(see test circuit, Figure 5)		1.7		A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

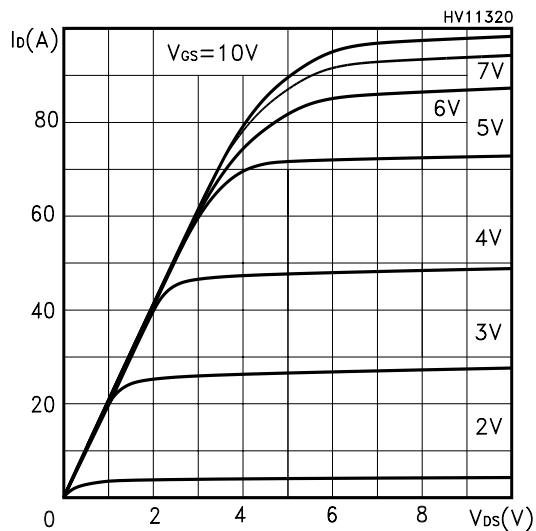
**Safe Operating Area**



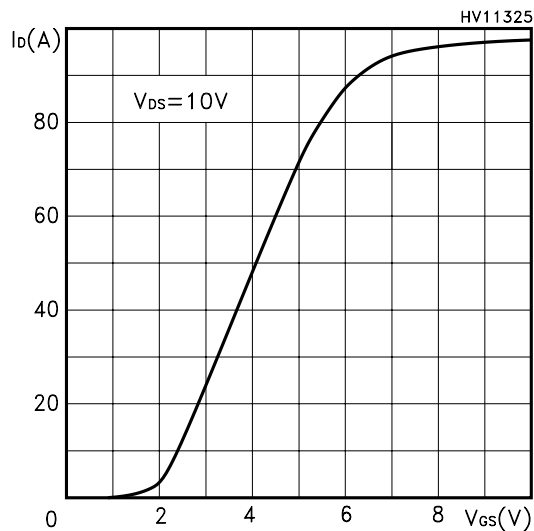
**Thermal Impedance**



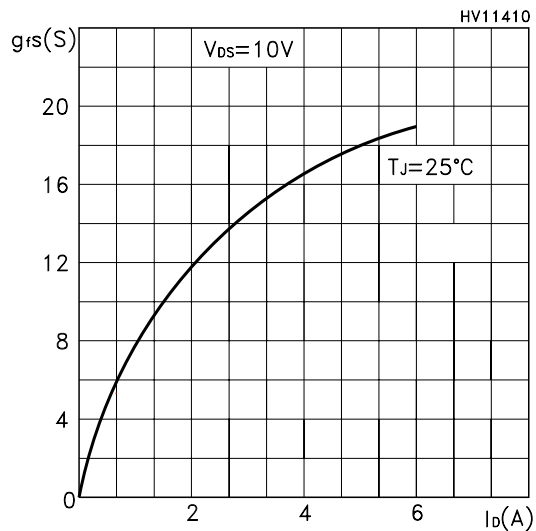
**Output Characteristics**



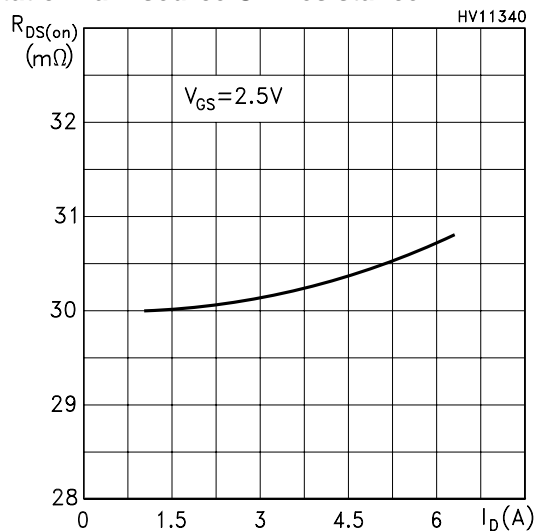
**Transfer Characteristics**



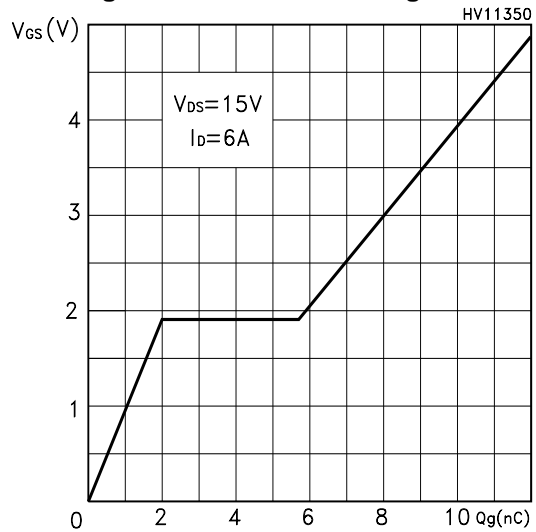
**Transconductance**



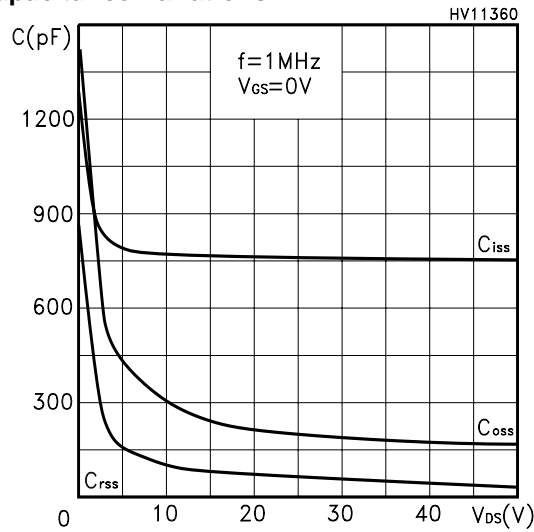
**Static Drain-source On Resistance**



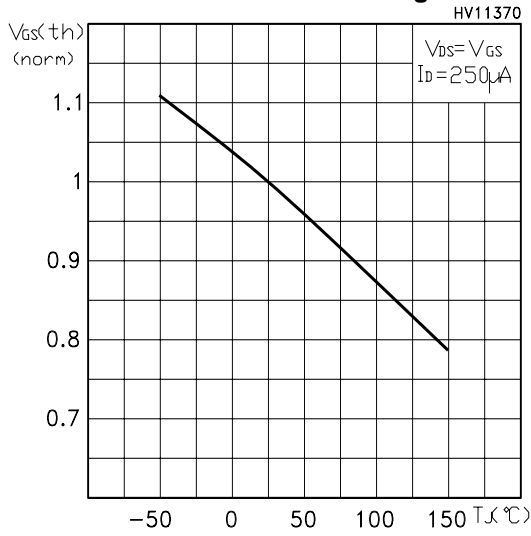
**Gate Charge vs Gate-source Voltage**



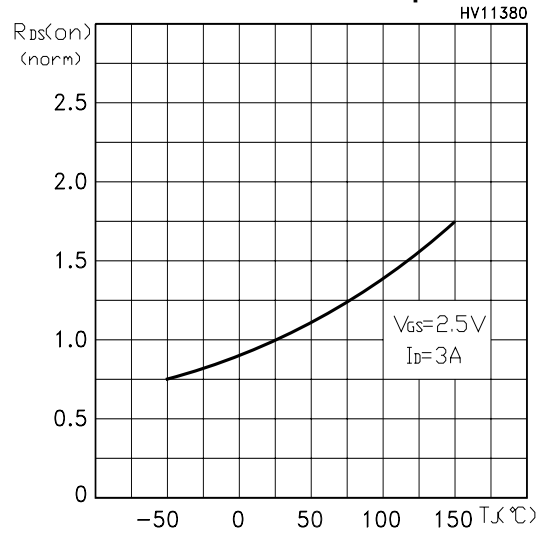
**Capacitance Variations**



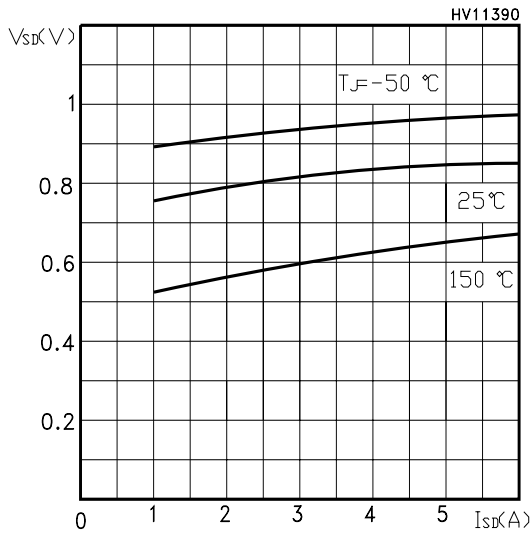
Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



**Fig. 1: Unclamped Inductive Load Test Circuit**



**Fig. 2: Unclamped Inductive Waveform**



**Fig. 3: Switching Times Test Circuit For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

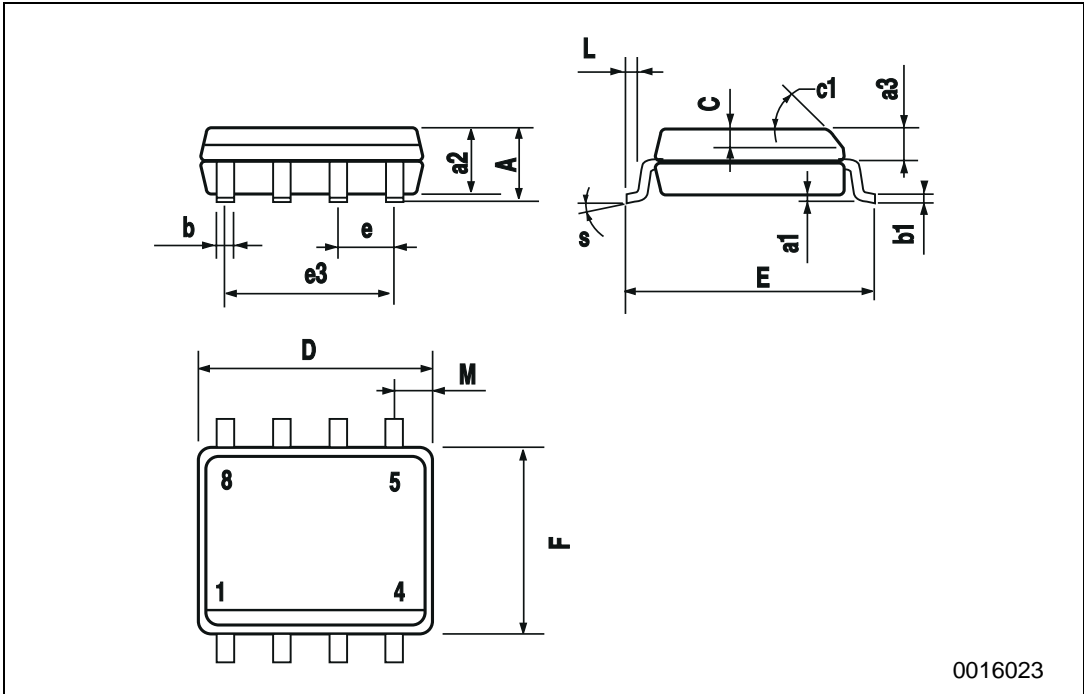


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



**SO-8 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2002 STMicroelectronics - Printed in Italy - All Rights Reserved  
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco  
Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

© <http://www.st.com>